

Ultra-long relaxation of a Kramers qubit formed in a bilayer graphene quantum dot

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Figures

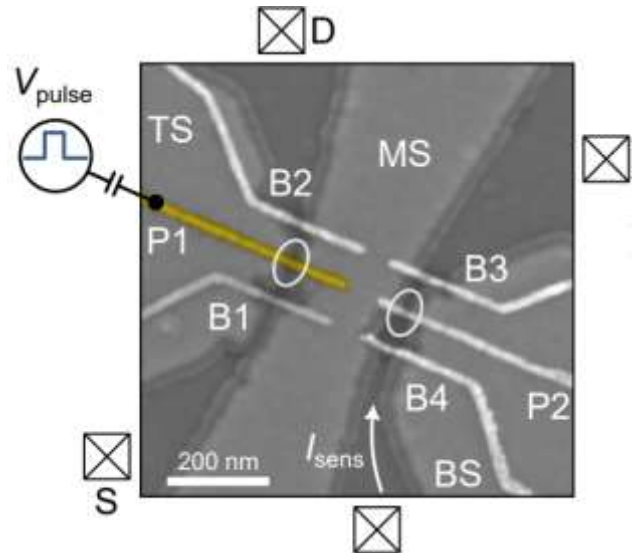


Figure 1: SEM false-colour image of the device. All labelled metallic gates and the graphite back gate (not shown) are DC-biased. The plunger gate P1 is additionally controlled by AC pulses.

Abstract

The intrinsic valley degree of freedom makes bilayer graphene a unique platform for emerging types of semiconducting qubits. The single-carrier quantum dot ground state exhibits a two-fold degeneracy where the two states have opposite spin and valley quantum numbers. By breaking the time-reversal symmetry of this ground state with an out-of-plane magnetic field, a novel type of qubit (Kramers qubit), encoded in the two-dimensional spin–valley subspace, becomes accessible. The Kramers qubit is robust against known spin- and valley-mixing mechanisms, as it requires a simultaneous change of both quantum numbers, potentially resulting in long relaxation and coherence times. We measure the relaxation time of a single carrier in the excited states of a bilayer graphene quantum dot at small (\sim mT) and zero magnetic fields. We demonstrate ultra-long spin-valley relaxation times of the Kramers qubit exceeding 30 s, which is about two orders of magnitude longer than the spin relaxation time of 400 ms. The demonstrated high-fidelity single-shot readout and long relaxation times are the foundation for novel, long-lived semiconductor qubits [1].

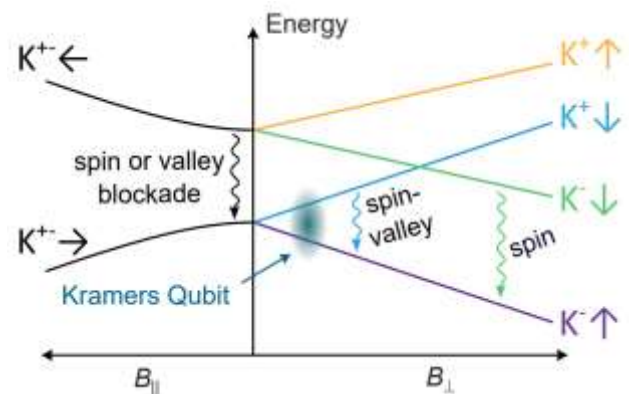


Figure 2: The energy spectrum of a single carrier in the BLG QD plotted as a function of in-plane and out-of-plane magnetic fields.

References

- [1] Artem O. Denisov, Veronika Reckova, Solenn Cances, Max J. Ruckriegel, Michele Masseroni, Christoph Adam, Chuyao Tong, Jonas D. Gerber, Wei